

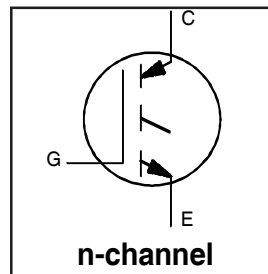
# IRG4BH20K-SPbF

INSULATED GATE BIPOLAR TRANSISTOR

Short Circuit Rated  
UltraFast IGBT

## Features

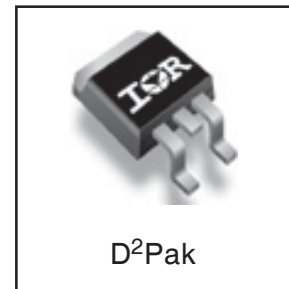
- High short circuit rating optimized for motor control,  $t_{sc} = 10\mu s$  @  $V_{CC} = 720V$ ,  $T_J = 125^\circ C$ ,  $V_{GE} = 15V$
- Combines low conduction losses with high switching speed
- Latest generation design provides tighter parameter distribution and higher efficiency than previous generations
- Industry standard D<sup>2</sup>Pak package
- Lead-Free



$V_{CES} = 1200V$
$V_{CE(on)} \text{ typ.} = 3.17V$
@ $V_{GE} = 15V, I_C = 5.0A$

## Benefits

- As a Freewheeling Diode we recommend our HEXFRED™ ultrafast, ultrasoft recovery diodes for minimum EMI / Noise and switching losses in the Diode and IGBT
- Latest generation 4 IGBT's offer highest power density motor controls possible



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	11	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	5.0	
$I_{CM}$	Pulsed Collector Current ①	22	
$I_{LM}$	Clamped Inductive Load Current ②	22	
$t_{sc}$	Short Circuit Withstand Time	10	$\mu s$
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$E_{ARV}$	Reverse Voltage Avalanche Energy ③	130	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
$T_J$	Operating Junction and	-55 to +150	$^\circ C$
$T_{STG}$	Storage Temperature Range		

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	2.1	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	40	
Wt	Weight	6 (0.21)	—	g (oz)

# IRG4BH20K-SPbF

International  
 Rectifier

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	1.13	—	V/°C	$V_{GE} = 0V, I_C = 2.5mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	3.17	4.3	V	$I_C = 5.0A$ $V_{GE} = 15V$
		—	4.04	—		$I_C = 11A$ See Fig.2, 5
		—	2.84	—		$I_C = 5.0A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.5	—	6.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/°C	$V_{CE} = V_{GE}, I_C = 1mA$
$g_{fe}$	Forward Transconductance ⑤	2.3	3.5	—	S	$V_{CE} = 100V, I_C = 5.0A$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	250	$\mu A$	$V_{GE} = 0V, V_{CE} = 1200V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ\text{C}$
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	28	43	nC	$I_C = 5.0A$
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	4.4	6.6		$V_{CC} = 400V$ See Fig.8
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	12	18		$V_{GE} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	23	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 5.0A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 50\Omega$
$t_r$	Rise Time	—	26	—		
$t_{d(off)}$	Turn-Off Delay Time	—	93	140		
$t_f$	Fall Time	—	270	400		
$E_{on}$	Turn-On Switching Loss	—	0.45	—	mJ	Energy losses include "tail" See Fig. 9,10,14
$E_{off}$	Turn-Off Switching Loss	—	0.44	—		
$E_{ts}$	Total Switching Loss	—	0.89	1.2		
$t_{sc}$	Short Circuit Withstand Time	10	—	—	$\mu s$	$V_{CC} = 720V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 50\Omega$
$t_{d(on)}$	Turn-On Delay Time	—	23	—	ns	$T_J = 150^\circ\text{C}$ , $I_C = 5.0A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail" See Fig. 10,11,14
$t_r$	Rise Time	—	28	—		
$t_{d(off)}$	Turn-Off Delay Time	—	100	—		
$t_f$	Fall Time	—	620	—		
$E_{ts}$	Total Switching Loss	—	1.7	—	mJ	
$L_E$	Internal Emitter Inductance	—	7.5	—	nH	Between lead and center of die contact
$C_{ies}$	Input Capacitance	—	435	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0MHz$
$C_{oes}$	Output Capacitance	—	44	—		
$C_{res}$	Reverse Transfer Capacitance	—	8.3	—		

### Notes:

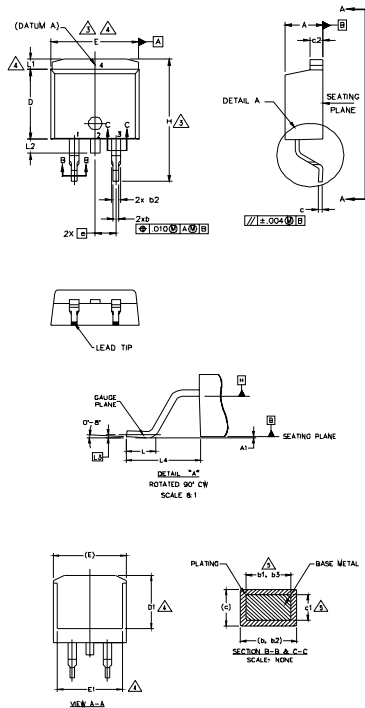
- ① Repetitive rating;  $V_{GE} = 20V$ , pulse width limited by max. junction temperature. ( See fig. 13b )
  - ②  $V_{CC} = 80\%(V_{CES})$ ,  $V_{GE} = 20V$ ,  $L = 10\mu H$ ,  $R_G = 50\Omega$ , (See fig. 13a)
  - ③ Repetitive rating; pulse width limited by maximum junction temperature.
  - ④ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
  - ⑤ Pulse width  $5.0\mu s$ , single shot.
- \* When mounted on 1" square PCB (FR-4 or G-10 Material ). For recommended footprint and soldering techniques refer to application note #AN-994.

# IRG4BH20K-SPbF

International  
**IR** Rectifier

## D<sup>2</sup>Pak Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
  4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
  5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
  6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
  7. CONTROLLING DIMENSION: INCH.
  8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	5
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	
c	0.38	0.74	.015	.029	5
c1	0.38	0.58	.015	.023	
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	-	.270	-	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	-	.245	-	4
e	2.54 BSC		.100 BSC		4
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	-	1.65	-	.066	4
L2	1.27	1.78	-	.070	
L3	0.25 BSC		.010 BSC		
L4	4.78	5.28	.188	.208	

**LEAD ASSIGNMENTS**

**HEXFET**

- 1.- GATE
- 2, 4.- DRAIN
- 3.- SOURCE

**IGBTs, CoPACK**

- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER

**DIODES**

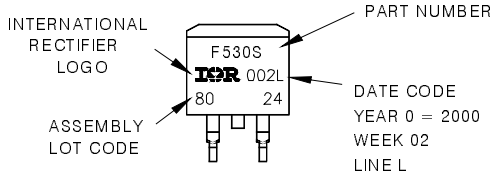
- 1.- ANODE \*
- 2, 4.- CATHODE
- 3.- ANODE

\* PART DEPENDENT.

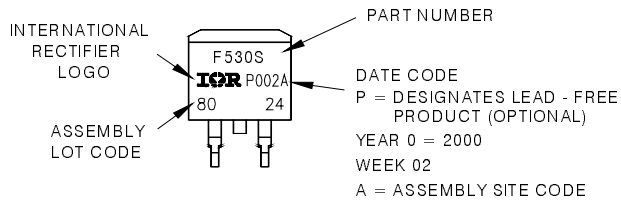
## D<sup>2</sup>Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH LOT CODE 8024 ASSEMBLED ON WW 02, 2000 IN THE ASSEMBLY LINE 'L'

Note: "P" in assembly line position indicates "Lead - Free"

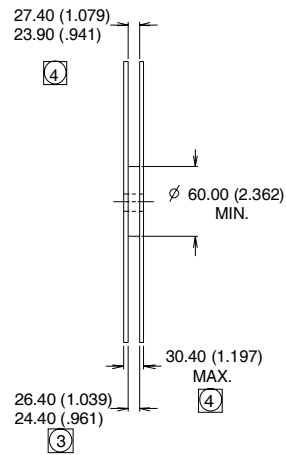
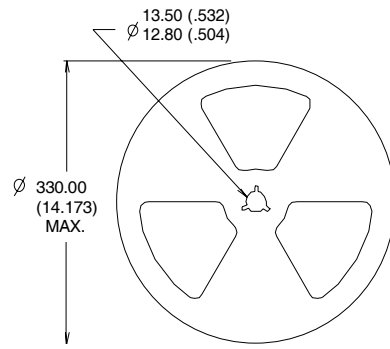
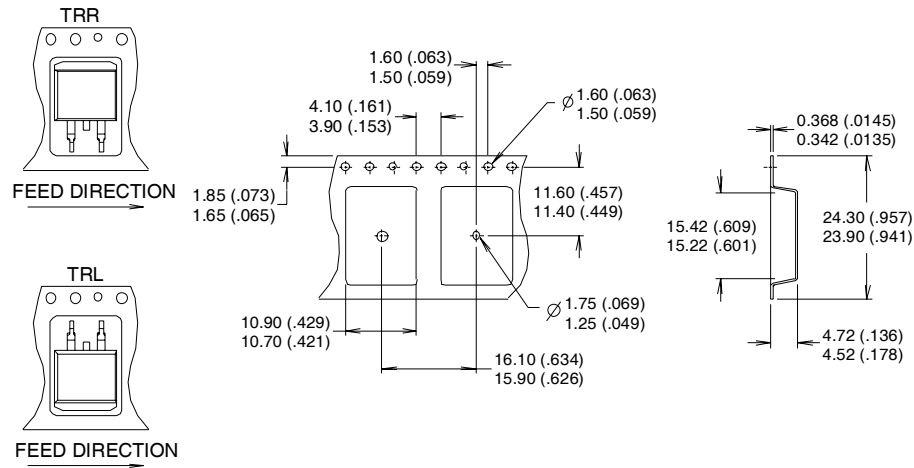


OR



**D<sup>2</sup>Pak Tape & Reel Information**

Dimensions are shown in millimeters (inches)



- NOTES:
1. COMFORMS TO EIA-418.
  2. CONTROLLING DIMENSION: MILLIMETER.
  - ③ DIMENSION MEASURED @ HUB.
  - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Data and specifications subject to change without notice.